

IGBT with Trench and Field-Stop technology

WGD15J120STB3

- V_{CES}=1200V
- I_C=15A@ T_C=100℃
- Very low V_{CEsat}
- 10µs short circuit capability
- Very soft, fast recovery diode
- High ruggedness
- RoHS compliant
- Halogen free

Applications

- Motor Drives
- General inverter
- Home Appliance Applications







Features	TO-247
	Tab



Package pin definition	1	2/Tab	3
	Gate	Collector	Emitter

Part	Package	Marking	Packing method	MPQ
WGD15J120STB3	TO-247	15J120STB3	Tube	30/Tube



1 Maximum Ratings

Table 1 Maximum rated Values(T_c=25℃ unless otherwise specified)

Parameter	Symbol	Condition	Values	Unit
Collector to Emitter Voltage	V _{CES}		1200	V
Gate to Emitter Voltage	V _{GES}		±20	V
Continuous Collector Current			30	А
Continuous Collector Current	I _C	T _C =100℃	15	А
Pulsed Collector Current ¹	I _{CM}		45	А
Diada Cantinuana Famuand Cumant			30	А
Diode Continuous Forward Current	l _F	T _C =100℃	15	А
Diode Maximum Forward Current ¹	I _{FM}		45	А
Mayiraura Daytar Dissination	P _{tot}		375	W
Maximum Power Dissipation		T _C =100℃	185	W
Operating Junction Temperature Range	Tυ		-55~+175	°C
Storage Temperature Range	T _{STG}		-55~+150	$^{\circ}$ C
Thermal Resistance, Junction to case for IGBT	R _{th(J-C)}		0.4	K/W
Thermal Resistance, Junction to case for Diode	R _{th(J-C)}		1.2	K/W

Notes:



^{1.} Pulse width limited by maximum junction temperature.



2 Electrical Characteristics, IGBT

Table 2 Characteristics Values(T_c=25℃ unless otherwise specified)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Collector to Emitter Breakdown Voltage	BVces	I _C =250µA, V _{GE} =0V	1200	-	-	V
		I _C =15A, V _{GE} =15V	-	1.80	2.30	V
Collector to Emitter Saturation Voltage	V _{CE(sat)}	I _C =15A, V _{GE} =15V, T _J =150℃	-	2.30	-	V
Gate Threshold Voltage	V _{GE(th)}	Ic=250µA, V _{GE} =V _{CE}	4.7	5.7	6.7	V
Zero Gate Voltage Collector current	I _{CES}	V _{CE} =1200V, V _{GE} =0V	-	-	250	μA
Gate to Emitter Leakage Current	I _{GES}	V _{GE} =±20V, V _{CE} =0V	-	-	±100	nA
Input Capacitance	Cies		-	1248	-	pF
Output Capacitance	Coes	f=1MHz, V _{CE} =30V, V _{GE} =0V	-	53	-	pF
Reverse Transfer Capacitance	Cres		-	10	-	pF
Total Gate charge	Q _G		-	81	-	nc
Gate to Emiter charge	QGE	Vcc=960V, Ic=15A, VgE=15V	-	11	-	nc
Gate to Collector charge	Q _{GC}		-	44	-	nc
Short Circuit Withstand Time	t _{sc}	V _{CC} =600V, V _{GE} =15V	-	10	-	μs
Turn-on Delay Time	t _{d(on)}		-	34	-	ns
Rising Time	t _r		-	28	-	ns
Turn-off Delay Time	t _{d(off)}	V _{CC} =600V, I _C =15A, V _{GE} =0/15V,	-	132	-	ns
Falling Time	t _f	R _G =10Ω, T _J =25℃ Inductive load	-	78	-	ns
Turn-on Switching Loss Energy	Eon		-	0.56	-	mJ
Turn-off Switching Loss Energy	E _{off}		-	0.55	-	mJ
Turn-on Delay Time	t _{d(on)}		-	34	-	ns
Rising Time	tr	Vcc=600V, Ic=15A, VgE=0/15V,	-	30	-	ns
Turn-off Delay Time	t _{d(off)}		-	164	-	ns
Falling Time	t _f	R _G =10Ω, T _J =150˚C Inductive load	-	120	-	ns
Turn-on Switching Loss Energy	Eon		-	0.69	-	mJ
Turn-off Switching Loss Energy	E _{off}		-	0.70	-	mJ





3 Electrical Characteristics, Diode

Table 3 Characteristics Values(T_c=25℃ unless otherwise specified)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
		I _F =15A, T _J =25℃	-	2.38	2.90	V
Diode Forward Voltage	VF	I _F =15A, T _J =150℃	-	2.00	-	V
Diode Peak Reverse Recovery Current	I _{RM}		-	9	-	Α
Diode Reverse Recovery Time	t _{rr}	I _F =15A di/dt=-340A/μs V _{CC} =600V T _J =25℃	-	70	-	ns
Diode Reverse Recovery Charge	Qrr		-	336	-	nC
Reverse Recovery Energy	Erec		-	59	-	μJ
Diode Peak Reverse Recovery Current	Irr		-	11	-	Α
Diode Reverse Recovery Time	t _{rr}	I _F =15A di/dt=-330A/μs V _{CC} =600V TJ=150℃	-	106	-	ns
Diode Reverse Recovery Charge	Qrr		-	611	-	nC
Reverse Recovery Energy	E _{rec}		-	117	-	μJ





4 Typical Characteristics diagrams

Fig.1 Typical output characteristic $I_C=f(V_{CE})$, $T_{vi}=25^{\circ}C$

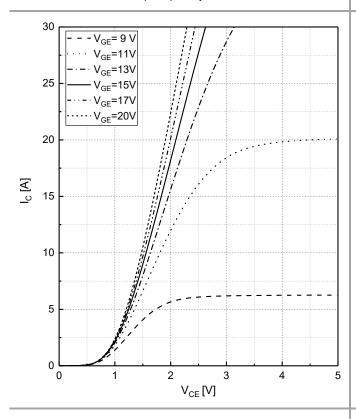


Fig.2 Typical output characteristic $I_C=f(V_{CE}), T_{vj}=150^{\circ}C$

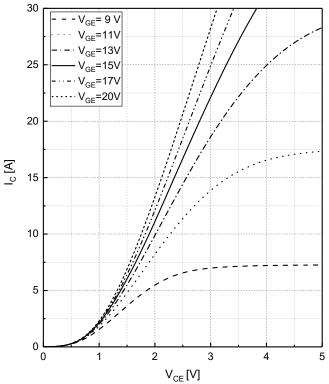


Fig.3 Typical transfer characteristic $I_C=f(V_{GE}), V_{CE}=20V$

10 V_{GE}[V]

T_J= 25 °C

T₁=150°C

25

20

10

5

0

I_c [A]

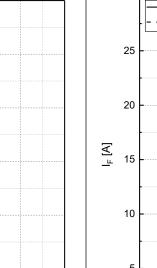


Fig.4 Typical I_F as a function of V_F $I_F=f(V_F)$

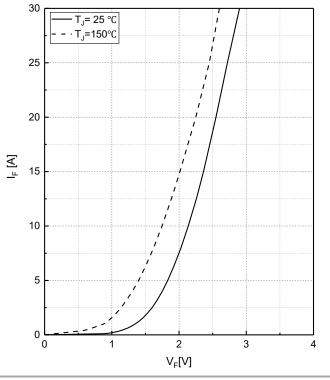
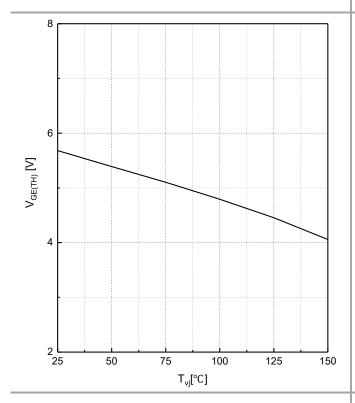




Fig.5 Typical $V_{GE(th)}$ as a function of T_{vj} V_{GEth} = $f(T_{vj})$, I_{C} =250 μ A

Fig.6 Typical V_{CEsat} as a function of T_{vj} V_{CEsat} =f(T_{vj}), V_{GE} =15V



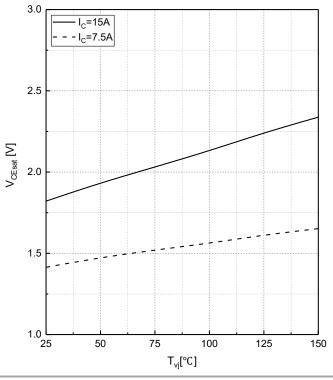
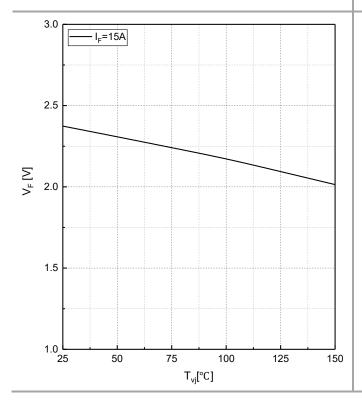


Fig.7 Typical V_F as a function of T_{vj} $V_F = f(T_{vj})$

Fig.8 Typical switching energy losses as a function of R_G E=f(R_G), V_{CC} =600V, I_C =15A, V_{GE} =0/15V, T_J =150 $^{\circ}$ C



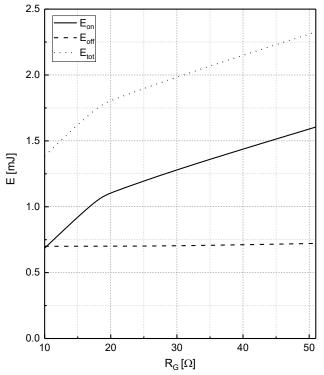
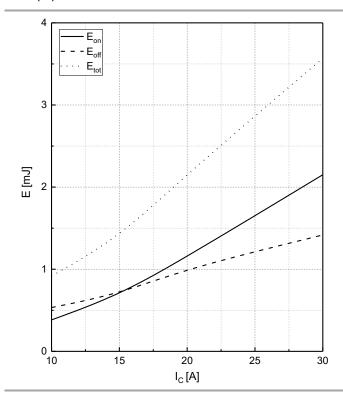




Fig.9 Typical switching energy losses as a function of $I_{\mathbb{C}}$

E=f(I_C), V_{CC} =600V, R_{G} =10Ω, V_{GE} =0/15V, T_{J} =150°C

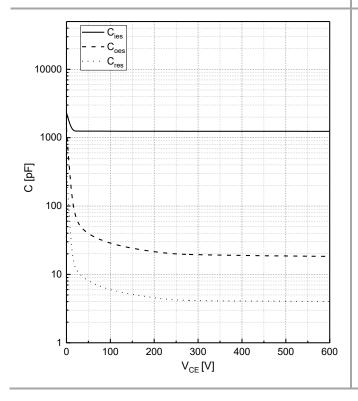
Fig.10 Typical Gate charge V_{GE} =f(Q_G), I_C =15A, V_{CC} =960V



15 12 9 6 3 75 Q_G[nC]

Fig.11 Typical capacitance as a function of V_{CE} C=f(V_{CE}), f=1MHz, V_{GE} =0V

Fig.12 Collector current as a function of case temperature $I_{C} = f(T_{vj})$



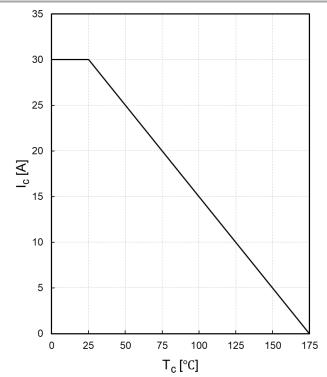
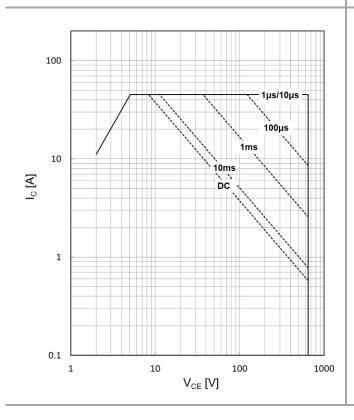
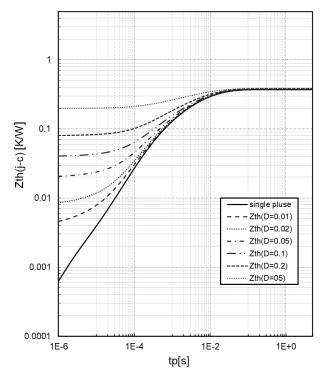




Fig.13 Forward bias safe operating area of IGBT T_c=25°C, T_{vj}≤175°C, V_{GE}=15V, single pluse

Fig.14 Transient thermal impedance of IGBT $Z_{th(j-c)}=f(t_p), D=t_p/T$

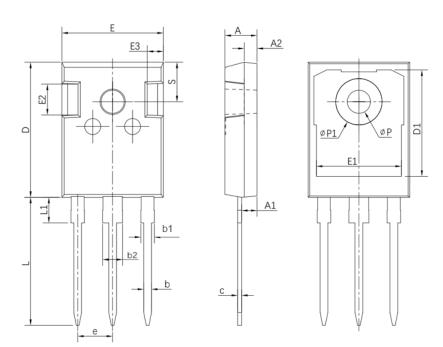








5 Package Outlines



SYMBOL	mm				
STIVIDUL	MIN	NOM	MAX		
Α	4.80	5.00	5.20		
A1	2.21	2.41	2.59		
A2	1.85	2.00	2.15		
b	1.11	1.21	1.36		
b1	1.91	2.01	2.25		
b2	2.91	3.01	3.25		
С	0.51	0.61	0.75		
D	20.80	21.00	21.30		
D1	16.25	16.55	16.85		
Е	15.50	15.80	16.10		
E1	13.00	13.30	13.60		
E2	4.80	5.00	5.20		
E3	2.30	2.50	2.70		
е	5.44BSC				
L	19.62	19.92	20.22		
L1	-	-	4.30		
ФР	3.40	3.60	3.80		
ФР1	-	-	7.30		
S	6.15BSC				

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Product Specification Statement

1. The product specification aims to provide users with a reference regarding various product parameters, performance, and usage. It presents certain aspects of the product's performance in graphical form and is intended solely for users to select product and make product comparisons, enabling users to better understand and evaluate the characteristics and advantages of the product. It does not constitute any commitment, warranty, or guarantee.

2.The product parameters described in the product specification are numerical values, characteristics, and functions obtained through actual testing or theoretical calculations of the product in an independent or ideal state. Due to the complexity of product applications and variations in test conditions and equipment, there may be slight fluctuations in parameter test values. WAYON shall not guarantee that the actual performance of the product when installed in the customer's system or equipment will be entirely consistent with the product specification, especially concerning dynamic parameters. It is recommended that users consult with professionals for product selection and system design. Users should also thoroughly validate and assess whether the actual parameters and performance when installed in their respective systems or equipment meet their requirements or expectations. Additionally, users should exercise caution in verifying product compatibility issues, and WAYON assumes no responsibility for the application of the product.

3.WAYON strives to provide accurate and up-to-date information to the best of our ability. However, due to technical, human, or other reasons, WAYON cannot guarantee that the information provided in the product specification is entirely accurate and error-free. WAYON shall not be held responsible for any losses or damages resulting from the use or reliance on any information in these product specifications. WAYON reserves the right to revise or update the product specification and the products at any time without prior notice, and the user's continued use of the product specification is considered an acceptance of these revisions and updates. Prior to purchasing and using the product, users should verify the above information with WAYON to ensure that the product specification is the most current, effective, and complete. If users are particularly concerned about product parameters, please consult WAYON in detail or request relevant product test reports. Any data not explicitly mentioned in the product specification shall be subject to separate agreement.

4.Users are advised to pay attention to the parameter limit values specified in the product specification and maintain a certain margin in design or application to ensure that the product does not exceed the parameter limit values defined in the product specification. This precaution should be taken to avoid exceeding one or more of the limit values, which may result in permanent irreversible damage to the product, ultimately affecting the quality and reliability of the system or equipment.

5. The design of the product is intended to meet civilian needs and is not guaranteed for use in harsh environments or precision equipment. It is not recommended for use in systems or equipment such as medical devices, aircraft, nuclear power, and similar systems, where failures in these systems or equipment could reasonably be expected to result in personal injury. WAYON shall assume no responsibility for any consequences resulting from such usage.

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